

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-532		SERIAL NO. 09/312,271	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Klaus Florian Schuegraf et al.			
				FILING DATE June 11, 1999		GROUP 2812	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
RP	AN			Ohnishi, K. et al., Improving Gate Oxide Integrity (GOI) of a W/Workfunction/poly-Si Stacked-Gate by Using Wet-Hydrogen Oxidation in 0.14- μ m CMOS devices, IEDM, 1998, pgs. 397-400.			
RP	AO			Kawada, K. et al., Water Vapor Generator By catalytic Reactor, pgs. 10-16.			
RP	AP			Wakabayashi, H. et al., An Ultra-Low Resistance and Thermal Stable W/pn-Poly-Si Gate CMOS Technology using SiTiN Buffer Layer, IEDM, 1998, pgs. 393-396.			
RP				Mura, Y. et al., Integration Technology of Polymetal (WWSiN/Poly-Si) Dual Gate CMOS for 1 Gbit DRAMs and Beyond, IEDM, 1998, pgs. 389-392.			
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Ron Pompey				4-2304			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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